Analog Electronic Circuits- 21EC34

IAT3 Solution-Feb 2023

1. SAR ADC

ADE

ADC converts an analog voltage to difficial outfort specified as 8, 10,12, 16. etc bit.

Š)

Successive-Approximation ADC.

Following figure Fig 5.3 slows a successiveapproximation type ADC, which uses a comparator, a successive approximation reguster, ortput latches and a DAC:

The errorit work as follows.

. At the start of a conversion eyele, the SAR is reset by holding the start (3) signal ligh.

. On the LOW. b. HIGH transmistor transmition, the most significant output bit 07 of the $SAGB4 \tilde{B}$ and

. The D/A converter then generates an analog equivalent to the Qq bit, which is compared with Vin.

. If the comparator onlight is low, that means DAC onlight > Vin and the SAR will clear its MSB Q7. On the other hand if comparator onlight is high, which means . DAC onlight 2 $\sqrt{2}$ the SAR will keep MSB Qq sel.

. Linitarly depending as on the comparator onfort, the is SAR with then keep either beep as or reset but Q6, on the next clock pulse LOW- he high.

. As soon this process is continued until the SAR Aries all the bits i.e $\mathbb{Q}_5, \mathbb{Q}_4, \mathbb{Q}_5, \mathbb{Q}_1, \mathbb{A} \mathbb{Q}_1$ and \mathbb{Q}_n . As soon as LSB Q , is forled, the SAR forces the conversion complete (CC) synd HIGH to indicate that the parallel output lines contains valid data.

- . The cc signal in turns enables the potch,
and digital data affect at the onlight of the latch, which gives the digital representation of the analog voltage Vin.
- . For 8 bit SAR type ADC eight clock fulne
6 required, for 12 bit, 12 clock fulse is
required and so on.

$_{\rm{clk}}$ **B3 B2 B1** BO₁ **VD** VA>VD **Decision VO** op 2.5 1.25 0.625 0.3125 $\mathbf{1}$ 0 \circ 0 $\mathbf{1}$ 2.5 No Reset $\mathbf 0$ $\overline{0}$ ö 1.25 **Set** 1.25 $\overline{2}$ ۵ 1 Yes o 1 $\mathbf{1}$ 1.875 **Yes** Set 1.875 $\overline{\mathbf{3}}$ 2.1875 No 1.875 0110 $\overline{4}$ 1 1 Reset SOC EDC ٠ Comparator $V_A = 2V$
 $V = 5$ $W =$ Successive $-\alpha$ **Malig lipit** Адрессиасов **Report** Step Size = 5/16 = 0.3125 Vb $+000$ %Error = (2-1.875)*100/2 $+ 0.99$ $(0.125*100)/2=6.2%$ DAC¹

Example

2. Give the circuit diagram, gain expression and frequency response plots of:-

- (a) First order Low pass filter
- (b) Second order Low pass filter
- (c) Wide band pass filter
- (d) Narrow band reject filter
- a) First order Lowpass

b) Second order Low pass

$$
\frac{V_O}{V_{in}} = A_F * \frac{\frac{1}{(R_2 C_2 C_3 R_3)}}{S^2 + \frac{(R_2 C_3 + R_2 C_2 + R_3 C_3 - R_2 C_2 A_F)S}{R_2 C_2 C_3 R_3} + \frac{1}{(R_2 C_2 C_3 R_3)}}
$$
\n
$$
f_H = \frac{1}{2\pi\sqrt{(R_2 C_2 C_3 R_3)}}
$$

d) Narrow band reject filter

3. What are the different turn on methods of SCR? Explain each of them in detail.

Turn-on methods A thypisita can be traned on from mon- conducting state to a conducting state in several ways :-1 Ferward valtage buggering - when VAK et mercand with gate ckt open, Is will have avalomene breakdown at kneat over voltage VB0 At this voltage, thysister changes from OFF to ON state.
2 Thermal taggerity - The indth of the depletion lager q a thejeister decreases on microaning the
function temperature. So wherethe VAK is very

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@ Radiation biggening (Light tonggening). Thypuster is bombarded by energy particles such external energy, elected shote print are generated which will increase the number of charge carriers Causing inflantaneous flow of current For this to rale of change q voldage (av) 4) du larggering - when ser is in farmand beard mode, Is will remain reverse beard. Is has the channels ester of a capacitar due to charges existing across the junction of the voltage impresses $x_c = \frac{dQ}{dt} = \frac{d}{dt}(c_j v) = C f \frac{dV}{dt} + V \frac{dC_i}{dt}$ Ci isconstant \therefore $\angle c = \sqrt{dV}$ secupatre soit rate of change of voltage, du is large, the device may turn on. By applying a posture Signal at the gate, the

Three lypes of gate biogering pulses are cal 3 Dc gate biggering - DC voetage of proper (a) De gate biggering - De voltage ;
magnitude and polarity and applied betweengate 16 Ac gate linggering - Mart used in all ac applications. Provides proper isolation between applications. Traveler phase angle conted will periode peoper firing angle (c) Pals gate biggering - Most popular method. A seguence q gate pulses are given to trenon A sequence of gate paras caerier frequency an SCR. This is known us used for isolation.
galing A transformer is used for isolation. gating A transformer is uniformer snightly,
There is no need & applying continuous snightly,

4. Draw the circuit and frequency response of a second order low pass filter. Derive an expression for the cut off frequency.

KCL Equations
 $V_{in} = (R_2 C_2 C_3 R_3 S^2 + C_3 R_2 S + C_3 R_3 S + R_2 C_2 S - R_2 C_2 S A_F + 1)V_1$ $\frac{V_{in} - V_a}{R_2} = C_2 S(V_a - V_0) + \frac{V_a - V_1 V_a - V_1}{R_2 R_2} = C_3 S V_1$ $V_a = (C_3R_3S + 1)V_1$ $V_{in} = (R_2C_2S+1)V_a + R_2*\frac{V_a-V_1}{R_2}-R_2C_2SV_0$ $V_{in} = (R_2C_2S + 1)V_a + R_2*\frac{V_a - V_1}{R_2} - R_2C_2SV_0$ $V_{in} = (R_2C_2S+1)V_a + R_2 * \frac{V_a - V_1}{R_3} - R_2C_2SV_o$ $V_{in} = (R_2C_2S + 1 + \frac{R_2}{R_3})V_a - V_1(\frac{R_2}{R_3} + R_2C_2SA_F)$ $V_{in} = (R_2C_2S + 1 + \frac{R_2}{R_2})(R_3C_3S + 1)V_1 - V_1(\frac{R_2}{R_2} + R_2C_2SA_F)$

$$
\frac{V_1}{V_{in}} = \frac{\frac{1}{(R_2C_2C_3R_3)}}{S^2 + \frac{(R_2C_3 + R_2C_2 + R_3C_3 - R_2C_2A_F)S}{R_2C_2C_3R_3} + \frac{1}{(R_2C_2C_3R_3)}}
$$

$$
\frac{V_0}{V_{in}} = A_F * \frac{\frac{1}{(R_2 C_2 C_3 R_3)}}{S^2 + \frac{(R_2 C_3 + R_2 C_2 + R_3 C_3 - R_2 C_2 A_F)S}{R_2 C_2 C_3 R_3} + \frac{1}{(R_2 C_2 C_3 R_3)}}
$$

$$
\omega_n = \frac{1}{\sqrt{(R_2 C_2 C_3 R_3)}} f_H = \frac{1}{2\pi \sqrt{(R_2 C_2 C_3 R_3)}}
$$

$$
\left| \frac{v_{out}}{V_{in}} \right| = \frac{A_F}{\sqrt{1 + (\frac{f}{f_H})^4}}
$$

$$
\frac{V_O}{V_{in}} = A_F * \frac{\frac{1}{RC^2}}{S^2 + \frac{(3 - A_F)S}{RC} + \frac{1}{RC^2}}
$$

$$
2\zeta = 3 - A_F
$$

For Butter-worth Approximation

$\zeta = 0.707$, then $A_F = 1.586$

5. Explain the static Anode – Cathode characteristics of SCR with circuit diagram and VI characteristics. Define Latching and Holding Currents.

Circuit diagram

Forward Blocking mode

In this mode of operation, the positive voltage is applied to the anode and the negative voltage applied to the cathode, there will not be any pulse applied to the gate, it will be kept in the open state. Once the voltage is applied, the junctions J1 and J3 will be forward biased and the junction J2 will be reverse biased. Since J2 is reverse biased the width of the depletion region increases and it acts as an obstacle for conduction, so only a small amount of current will be flowing from J1 to J3.

Forward Conduction Mode

The Forward Conduction Mode is the only mode at which the SCR will be in the ON state and will be conducting. We can make the SCR conduct in two different ways, one we can increase the applied forward biasWhen we increase the Applied forward bias voltage between the anode and cathode the junction J2 will be depleted due to the avalanche breakdown and the SCR will start conducting. We are not able to do this for all the applications and this method of activating the SCR will eventually reduce the lifetime of the SCR.If you want to use the SCR for low voltage applications you can apply a positive voltage to the gate of the SCR. The applied positive voltage will help the SCR to move to the conduction state. During this mode of operation, the SCR will be operating in forward bias and current will be flowing through it. voltage beyond the breakdown voltage or else we can apply a positive voltage to the gate terminal.

Reverse Blocking Mode

In the reverse blocking mode, the positive voltage is applied to the Cathode (-) and the Negative voltage is given to the Anode (+), There will not be any pulse given to the gate, it will be kept as an open circuit. During this mode of operation the Junctions J1 and J3 will be reverse biased and the junction J2 will be forward biased. Since the junctions J1 and J3 are reverse biased there will not be any current flowing through the SCR. Although there will be a small leakage current flowing due to the drift charge carriers in the forward-biased Junction J2, it is not enough to turn on the SCR.

1. Breakover Voltage- It is the minimum forward voltage, gate being open, at which SCR starts conducting heavily i.e. turned on. Commercially available SCRs have breakover voltages from about 50 V to 500 V.

2. Peak Reverse Voltage (PRV)- It is the maximum reverse voltage (cathode positive w.r.t. anode) that can be applied to an SCR without conducting in the reverse direction.

Latching current of forward biased SCR is the minimum current which anode current must attain to continue to remain in forward conduction mode even when gate current is removed.

Holding current of SCR or thyrsistor is that minimum value of current below which anode current must fall to come in OFF state.

6. Explain the working of UJT and how UJT firing circuit is used for triggering an SCR.

The Unijunction Transistor or UJT for short, is a solid state three terminal device that can be used in gate pulse, timing circuits and trigger generator applications to switch and control either thyristors and triac's for AC power control type applications. Like diodes, unijunction transistors are constructed from separate P-type and N-type semiconductor materials forming a single (hence its name Uni-Junction) PN-junction within the main conducting N-type channel of the device.

Unijunction Transistor (UJT)

• For a Unijunction transistor, the resistive ratio of R_{B1} to R_{BB} is called the intrinsic stand-off ratio (η) .

$$
\eta = \frac{R_{B1}}{R_{B1} + R_{B2}}
$$

• Typical standard values of n range from 0.5 to 0.8 for most common UJT's.

Characteristics

 If a small positive input voltage which is less than the voltage developed across resistance, RB1 (ηVBB) is now applied to the Emitter input terminal, the diode p-n junction is reverse biased, thus offering a very high impedance and the device does not conduct. The UJT is switched "OFF" and zero current flows.

However, when the Emitter input voltage is increased and becomes greater than VRB1 (or ηVBB + 0.7V, where 0.7V equals the p-n junction diode volt drop) the p-n junction becomes forward biased and the unijunction transistor begins to conduct. The result is that Emitter current, ηIE now flows from the Emitter into the Base region.

The effect of the additional Emitter current flowing into the Base reduces the resistive portion of the channel between the Emitter junction and the B1 terminal. This reduction in the value of RB1 resistance to a very low value means that the Emitter junction becomes even more forward biased resulting in a larger current flow. The effect of this results in a negative resistance at the Emitter terminal.

UJT Firing Circuit

It is the most common method of triggering the SCR. The prolonged pulses at the gate using R and RC triggering methods cause more power dissipation at the gate. So by using UJT (Uni Junction Transistor) as triggering device the power loss is limited as it produce a train of pulses. The RC network is connected to the emitter terminal of the UJT which forms the timing circuit. The capacitor is fixed while the resistance is variable and hence the charging rate of the capacitor depends on the variable resistance means that the controlling of the RC time constant.

The UJT is often used in the timing and triggering circuits. Figure A shows the circuit diagram for the UJT relaxation oscillator. When the switch S is kept closed, the capacitor C is charged through resistance R towards voltage VDC. The voltage across capacitor in a given time depends upon circuit time constant RC.

When the voltage across capacitor becomes equal to peak point voltage, the emitter diode is forward biased and UJT conducts. As soon as the UJT starts to conduct, the capacitor discharges through inter base resistance RB1 and the resistance R1. The discharging time constant of the capacitor is very small as compared to charging time constant. The discharging time constant of the capacitor is very small as compared to charging time constant. When the voltage across capacitor becomes less than the valley point voltage during discharging of the capacitor, the UJT comes in to non-conducting state. (It means that the UJT remains in conducting state until the emitter current drops below valley current).

The capacitor charging and discharging waveform is shown in the Figure A in which time t1 denotes for charging time and time t2 denotes for discharging time of the capacitor.

As the discharging time of the capacitor is very small as compared to charging time, the time required to complete one cycle is considered only for charging time of the capacitor.

 $T = RC$ Loge ($Vdc / (Vdc - Vp)$)

As Vp = ηVdc + VD

Where Vp = Peak point voltage

η = Intrinsic stand off ratio

VD = Threshold voltage of the diode

 $T = RC$ Loge (Vdc /(Vdc – ηVdc – VD))

As VD is small, it is neglected.

T = RC Loge $(1/(1 - \eta))$

7. What is commutation? What are the different types of Commutation? Explain class A commutation in detail.

The process of turning of SCR is called commutation.

Me thools Tusin off Forced Commutation Natural Commutation Natural - A given in the ext chagram le transl will be ac-During the half classification class class B ep sagnal will be ac-during the they the if you to regative half Vin Q Vont narott

k forced Commutation (class A) This type & commutation were LC Components in Series with the load. We can have two continuations of class A circuit. O when the imparable with Capacitée @ When e_L is in series with a both the circuit forms an underdamped resonant Capacito charges gradually brozy curcunt. E_{dc} ϵ_{dc} $C \rightarrow$ Charges to Ede XO. instally During that lives $\mathcal{L}(t)$ MAR ON ESTAT Vc 1 the 4 Ga ω_{hom} V_c = Inductor then b chaves C I N But it an potaming. one addition for three in it which having V voltage to c so expansion ENT CLERK

when an underdamped resonant circuit useded by a de source, the envient will automatically become sero after some time. The thyrister when ON carries only the
changing current of capacitor c, and will soon reading
to a value lever than the holding current of the ex. This will switch of the thyrister (SCR). The time for switching off the clearce is determined by the resonant frequency which in turn depends aparthe Land C Components and the total lead nembouce

8. With a neat circuit diagram, explain the working of a Resistance Firing circuit. Determine the trigger angle α for the following specifications:- Ig(min) = 0.1mA, Vg(min) = 0.5 V. The diode is silicon and the peak amplitude of the input is 24 volts. Rv = $100k\Omega$, Rmin = 10 k Ω .

Numerical Part:

The first step is to determine the instantaneous value of e_s at which Solution: triggering will occur. At the SCR trigger point, $V_{\text{g}(min)} = 0.5 \text{V}$ and $I_{\text{g}(min)} = 0.1 \text{ mA}$. Using KVL around the gate circuit, we have

$$
e_s = I_g (R_V + R_{min}) + V_D + V_g
$$

At the trigger point,

 $e_{\text{stringger}}$ = 0.1 mA (110 kΩ) + 0.7V + 0.5V = 12.2 V. Since e_i is a sine-wave, it obeys the expression

$$
e_s = E_{\text{max}}
$$
. sin $\omega t = E_{\text{max}}$. sin $(2\pi ft)$

where $2\pi ft$ is the phase angle at any instant of time. For our purposes, this angle is α . Thus, $E_{\text{max}} = 24$ V,

$$
e_s = 24 \sin \alpha
$$
 \therefore 12.2 = 24 sin α .

$$
\sin \alpha = \frac{12.2}{24} \qquad \therefore \quad \alpha = 30.6^{\circ}.
$$

Remissionar faing circuit - The annul in hefigure Shows a simple method of far varying the brigger angle and thereby the power to the lead. Instead of wing a gate pulse to tagger the sck, gate werent is soupplied by an ac voltage source es, through Rosin Ry and dide D.

(1) As es gres pontus, SCR is FB. It will not

(ii) es forward brasses D, allowing gate current to

Start flowing

(iii) when Ig reacher, Ignum required to trigger the SCR will tuen ON and EL will be equal to ls

(N) SCR hemains ON till the +ve half cycle is over and the when is goes to gere, lead current & also seduces. when the lead current gas below holding award, ser turns off.

(v) ser remains in the off state for the whole -ve half cycle and will two an only when Ignin biggers SER again. (VI) The purpose of dieds is to prevent the gate-cathode Everence been from exceeding peak revenu voltage during -ve half cycle of ls. (Vii) The sequence is repeated. If Ru is increased, then gate current will reach its brigger value Ignin for a greater value of les making the SCR to trun off at a later stage The the funing angle & will increase Roman is seguined to to ensure that the peak gate awarent of the thyrister Igm is not exceeded. $R_{min} \n\mathbb{Z}$ $\frac{t_{max}}{\mathbb{Z}_{gm}}$